



PARA LIGHT

LED Component

IR Emitter & Detector & UVC



PARA LIGHT ELECTRONICS CO., LTD.

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Company Profile

- Established in 1987
- Chairman : Mr. David Ma
- Capital : USD 37million
- No. of Employee : 1028

Founded in 1987, PARA LIGHT is now a global innovator and leader in visible and invisible LED fields. With two manufacturing plants certified with ISO 14001, ISO 9001, TS16969, and also complies with REACH and RoHS.

We offer advanced and beyond expectation R&D services based on the strongest lineup ever of 1,028 employees located in different countries and cities that includes more than 70 professional engineers, and 80 Quality Assurance squad.

About the product category, from the elementary LED component to further appliance such as UV sensor, LED back light, integrated light module, commercial lighting, automotive lighting and any lighting solution, PARA LIGHT keeps growing and expanding the products diversity in response to the global industry or market trend.

Taiwan HQ



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Quality Certification



IATF16949



ISO9001



ISO14001



Through Hole Type

Infrared Emitting Diode
3mm / 5mm / 8mm

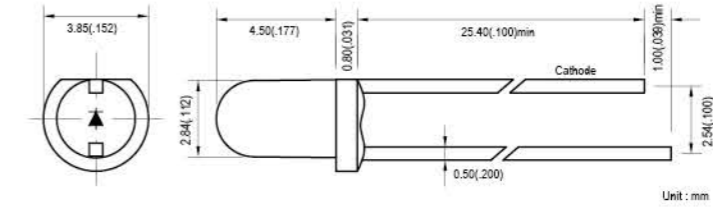


Application

- Remote Controller
- IP-Camara
- CCTV



Through Hole Type



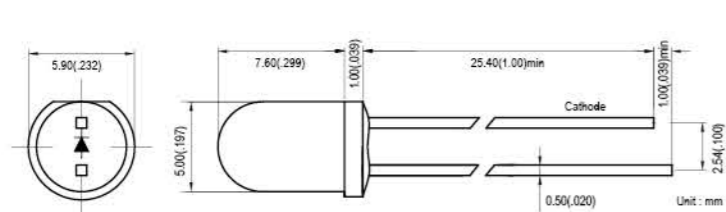
3mm L-31XXIR4X 850nm

Part No.	Wavelength λ_d (nm)	Viewing Angle (deg.)	Radiation Intensity I_e (mW/sr)		Typ. Forward Voltage V_f (V)	Forward Current I_f (mA)
			Min.	Typ.		
L-314EIR4C	850 nm	20	20	70	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-316EIR4C	850 nm	30	8	15	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-318EIR4C	850 nm	40	20	70	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-319EIR4C	850 nm	20	10	20	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-31AEIR4C	850 nm	50	4	10	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20

3mm L-31XXIR1X 940nm

Part No.	Wavelength λ_d (nm)	Viewing Angle (deg.)	Radiation Intensity I_e (mW/sr)		Typ. Forward Voltage V_f (V)	Forward Current I_f (mA)
			Min.	Typ.		
L-314EIR1C	940 nm	20	7	12	1.2@ $I_f=20$ mA 1.4@ $I_f=100$ mA	20
L-316EIR1C	940 nm	30	6	15	1.2@ $I_f=20$ mA 1.4@ $I_f=100$ mA	20
L-318EIR1C	940 nm	40	6	18	1.2@ $I_f=20$ mA 1.4@ $I_f=100$ mA	20
L-314EIR1BC	940 nm	20	2	6	1.2@ $I_f=20$ mA 1.4@ $I_f=100$ mA	20
L-316EIR1BC	940 nm	30	6	15	1.2@ $I_f=20$ mA 1.4@ $I_f=100$ mA	20
L-318EIR1C	940 nm	40	4	8	1.2@ $I_f=20$ mA 1.4@ $I_f=100$ mA	20

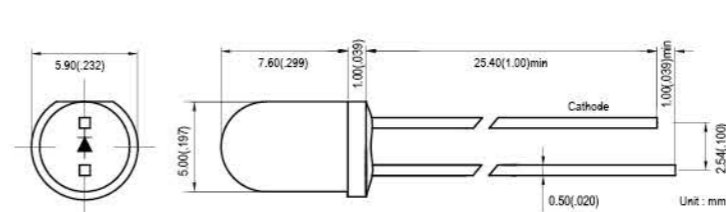
Through Hole Type



5mm L-51XXIR1X 940nm

Part No.	Wavelength λ_d (nm)	Viewing Angle (deg.)	Radiation Intensity I_e (mW/sr)		Typ. Forward Voltage V_f (V)	Forward Current I_f (mA)
			Min.	Typ.		
L-514EIR1C	940 nm	20	17	28	1.2@ $I_f=20$ mA 1.4@ $I_f=100$ mA	20
L-516EIR1C	940 nm	30	2	22	1.2@ $I_f=20$ mA 1.4@ $I_f=100$ mA	20
L-518EIR1C	940 nm	40	6	12	1.3@ $I_f=20$ mA 1.5@ $I_f=100$ mA	20
L-51CEIR1C	940 nm	60	4	8	1.3@ $I_f=20$ mA 1.5@ $I_f=100$ mA	20
L-514EIR1BC	940 nm	20	15	30	1.2@ $I_f=20$ mA 1.4@ $I_f=100$ mA	20
L-516EIR1BC	940 nm	30	12	20	1.2@ $I_f=20$ mA 1.4@ $I_f=100$ mA	20
L-518EIR1BC	940 nm	40	8	18	1.2@ $I_f=20$ mA 1.4@ $I_f=100$ mA	20
L-51AEIR1BC	940 nm	50	2	5	1.2@ $I_f=20$ mA 1.4@ $I_f=100$ mA	20

Through Hole Type



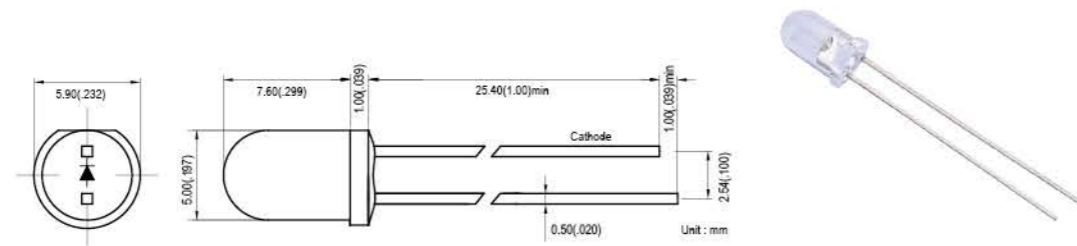
5mm L-51XGIR4XX 850nm

Part No.	Wavelength λ_d (nm)	Viewing Angle (deg.)	Radiation Intensity I_e (mW/sr)		Typ. Forward Voltage V_f (V)	Forward Current I_f (mA)
			Min.	Typ.		
L-514GIR4C	850 nm	20	60	175	1.4@ $I_f=20$ mA 1.5@ $I_f=100$ mA	100
L-516GIR4C	850 nm	30	30	80	1.4@ $I_f=20$ mA 1.5@ $I_f=100$ mA	100
L-518GIR4C	850 nm	40	60	85	1.4@ $I_f=20$ mA 1.5@ $I_f=100$ mA	100
L-51AGIR4C	850 nm	50	28	40	1.4@ $I_f=20$ mA 1.5@ $I_f=100$ mA	100
L-514GIR4BC	850 nm	20	127	170	1.4@ $I_f=20$ mA 1.5@ $I_f=100$ mA	100
L-516GIR4BC	850 nm	30	112	160	1.4@ $I_f=20$ mA 1.5@ $I_f=100$ mA	100
L-518GIR4BC	850 nm	40	55	85	1.4@ $I_f=20$ mA 1.5@ $I_f=100$ mA	100

5mm L-51XXIR3X 865nm

Part No.	Wavelength λ_d (nm)	Viewing Angle (deg.)	Radiation Intensity I_e (mW/sr)		Typ. Forward Voltage V_f (V)	Forward Current I_f (mA)
			Min.	Typ.		
L-514EIR3C	865 nm	20	30	50	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-516EIR3C	865 nm	30	12	30	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-518EIR3C	865 nm	40	10	22	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-51AEIR3C	865 nm	50	10	20	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-514EIR3BC	865 nm	20	25	45	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-516EIR3BC	865 nm	30	12	25	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-518EIR3BC	865 nm	40	10	20	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-51AEIR3BC	865 nm	50	10	18	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20

Through Hole Type



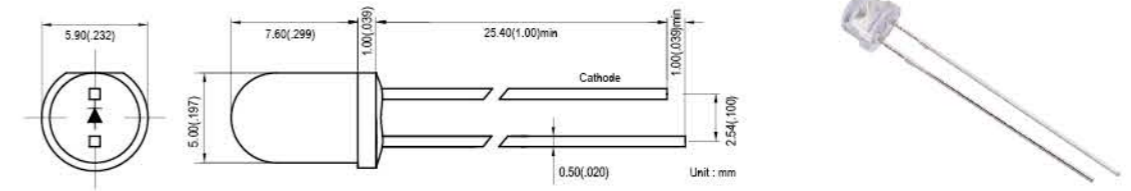
5mm L-51XXIR2X 880nm

Part No.	Wavelength λ_d (nm)	Viewing Angle (deg.)	Radiation Intensity I_e (mW/sr)		Typ. Forward Voltage V_f (V)	Forward Current I_f (mA)
			Min.	Typ.		
L-514EIR2C	880 nm	20	17	28	1.3@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-516EIR2C	880 nm	30	2	7	1.3@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-518EIR2C	880 nm	40	20	50	1.3@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-51AEIR2C	880 nm	50	4	10	1.3@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-514EIR2BC	880 nm	20	15	30	1.3@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-516EIR2BC	880 nm	30	15	30	1.3@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-518EIR2BC	880 nm	40	8	21	1.3@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-51AEIR2BC	880 nm	50	4	8	1.3@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20

5mm L-51XXIR4X 850nm

Part No.	Wavelength λ_d (nm)	Viewing Angle (deg.)	Radiation Intensity I_e (mW/sr)		Typ. Forward Voltage V_f (V)	Forward Current I_f (mA)
			Min.	Typ.		
L-514EIR2C	850 nm	20	25	45	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-516EIR2C	850 nm	30	14	45	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-518EIR2C	850 nm	40	10	20	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-51AEIR2C	850 nm	50	8	25	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-514EIR2BC	850 nm	20	8	20	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-516EIR2BC	850 nm	30	20	70	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-518EIR2BC	850 nm	40	12	40	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-51AEIR2BC	850 nm	50	12	35	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-51AEIR2BC	850 nm	50	10	25	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20

Through Hole Type

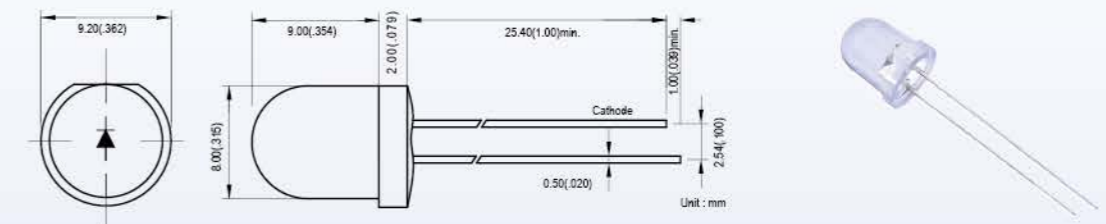


5mm L-5PGEIRXX 850nm

Part No.	Wavelength λ_d (nm)	Viewing Angle (deg.)	Radiation Intensity I_e (mW/sr)		Typ. Forward Voltage V_f (V)	Forward Current I_f (mA)
			Min.	Typ.		
L5PGEIR4C	850 nm	65	4	8	1.2	20

5mm L-5PGEIRXX 940nm

Part No.	Wavelength λ_d (nm)	Viewing Angle (deg.)	Radiation Intensity I_e (mW/sr)		Typ. Forward Voltage V_f (V)	Forward Current I_f (mA)
			Min.	Typ.		
L5PGEIR1C	850 nm	80	2	4	1.2	20



8mm L-51XXIR4X 850nm

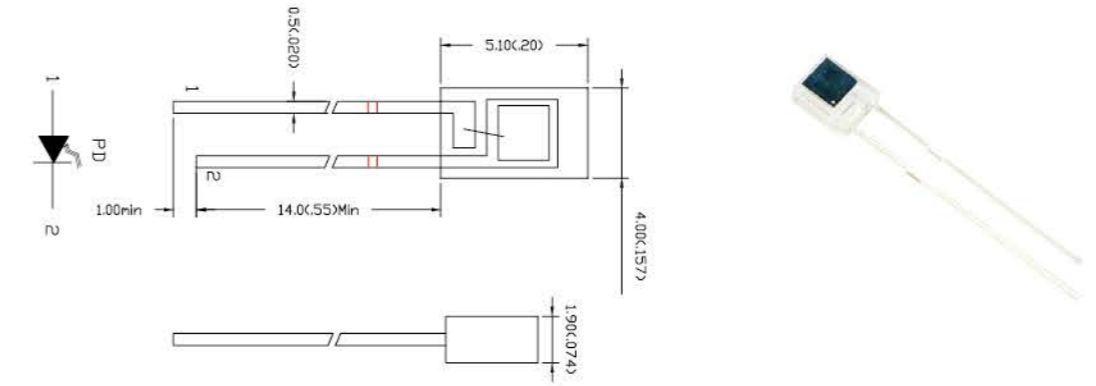
Part No.	Wavelength λ_d (nm)	Viewing Angle (deg.)	Radiation Intensity I_e (mW/sr)		Typ. Forward Voltage V_f (V)	Forward Current I_f (mA)
			Min.	Typ.		
L-814EIR4C	850 nm	20	32	50	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-816EIR4C	850 nm	30	10	35	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-818EIR4C	850 nm	40	15	25	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-81AEIR4C	850 nm	50	8	14	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20

Side view DIP(through hole) LED



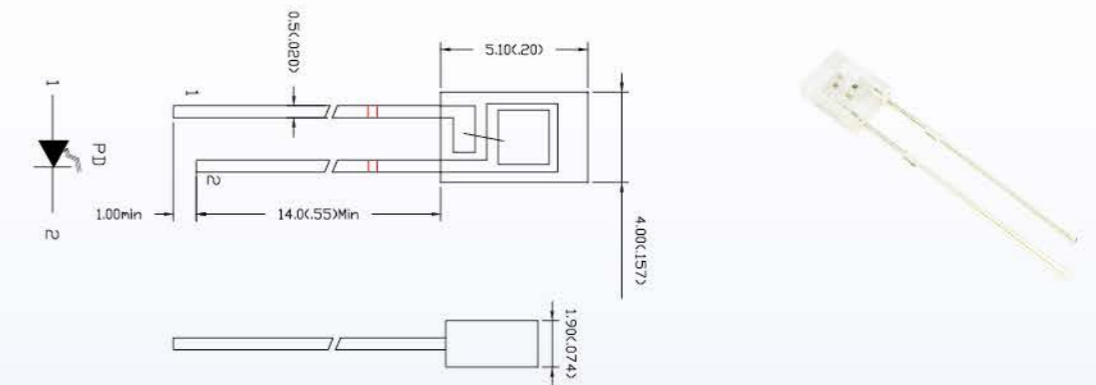
Application
- Pulse oximeter

Side view DIP(through hole) LED



LSC1R9PD1C

Lens Type	Reverse Breakdown BVR(V) $E_e=0 \text{ mW/cm}^2$ IR=100 μ A	Total Capacitance CT(pF) $E_e=0 \text{ mW/cm}^2$ VR=3V F=1MHZ	Max. Collector Dark Current I_{CEO} (nA) @ $V_{CE}=10\text{V}; E_e=0 \text{ mW/cm}^2$	Max. Collector-Emitter Saturation Voltage $V_{CE(S)}$ (V) @ $I_C=2\text{mA}; E_e=5 \text{ mW/cm}^2$	Typ. On State Collector Current I_C (mA) @ $V_{CE}=5\text{V}; E_e=1 \text{ mW/cm}^2$	Spectral Sensitivity Wavelength λ_p (nm)		
						Min.	Typ.	Max.
Water Clear	170	7.3	5	0.35	18	400	1100	



LSC2HIRC

Lens Type	Wavelength λ_d (nm)		Typ. Radiation Intensity I_e (mW/sr)		Typ. Forward Voltage V_F (V)		Forward Current I_F (mA)		Viewing Angle (deg.)
	R	IR	R	IR	R	IR	R	IR	
Water Clear	660 nm	905 nm	60	50	2.6	1.6	30	50	-



IR Emitter PLCC

IR 2835

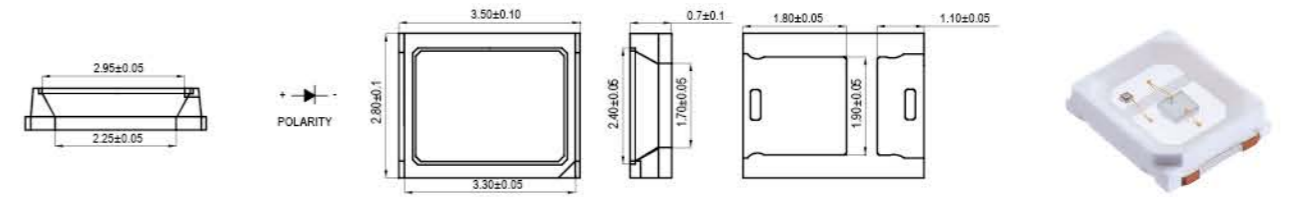


Application

- IP-Camera
- CCTV
- Drowsy Driver Detection
- Iris Recognition
- Face Recognition
- AR / VR / Gesture Recognition / VCSEL 3D Sensing (TOF)
- Vein Stria Recognition

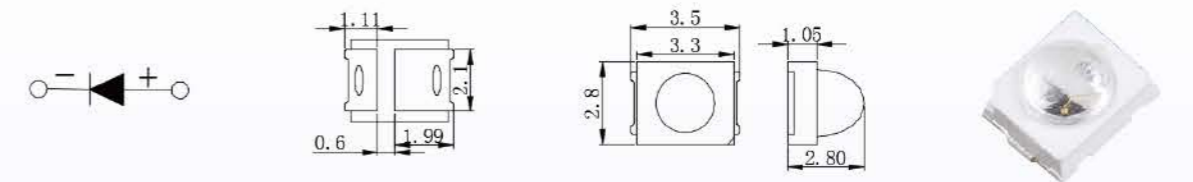


IR Emitter PLCC



LT2835 2.8x3.5x0.7mm

Part No.	Wavelength λ_d (nm)	Lens Type	Viewing Angle (deg.)	Typ. Radiation Intensity I_e (mW/sr)	Typ. Forward Voltage V_F (V)	Forward Current I_F (mA)
L-T2835IR4CT-20	850 nm	Water Clear	130	35	1.6	250
L-T2835IR4CT-24	850 nm	Water Clear	130	24	1.6	150



LT2835 2.8x3.5x2.42mm

Part No.	Wavelength λ_d (nm)	Package	Viewing Angle (deg.)	Radiation Intensity (mW)	Typ. Forward Voltage V_F (V)	Forward Current I_F (mA)
L-T2835IR4CT-30	850 nm	Water Clear	30	80~140	1.2~1.7	150
L-T2835IR4CT-60	850 nm	Water Clear	60	80~140	1.2~1.7	150
L-T2835IR4CT-90	850 nm	Water Clear	90	60~100	1.2~1.7	150

Phototransistor

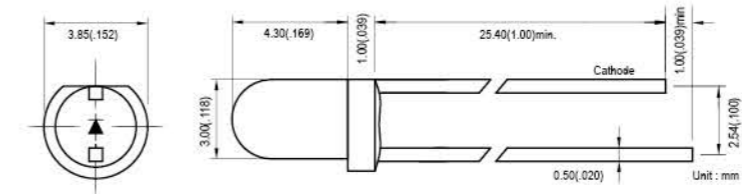
3.0mm / 5.0mm
L-31ROPT1X / L-51ROPT1X



- Application
- Photo-Switch
 - Detecting Object
 - Decoder

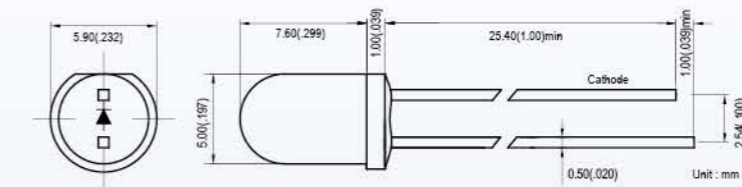


Phototransistor



L-31ROPT1X

Part No.	Min. Collector-Emitter Breakdown Voltage BV_{CEO} (V) @ $I_C=100\mu A$; $E_e=0$ mW/cm ²	Min. Emitter-Collector Breakdown Voltage BV_{ECO} (V) @ $I_C=100\mu A$; $E_e=0$ mW/cm ²	Max. Collector Dark Current I_{CEO} (nA) @ $V_{CE}=10V$; $E_e=0$ mW/cm ²	Max. Collector-Emitter Saturation Voltage $V_{CE(S)}$ (V) @ $I_C=2mA$; $E_e=0.5$ mW/cm ²	Typ. On State Collector Current I_C (mA) @ $V_{CE}=5V$; $E_e=0.1$ mW/cm ²	Spectral Sensitivity Wavelength λ_p (nm)		
						Min.	Typ.	Max.
L-31ROPT1C	30	5	100	0.4	4	400		1050
L-31ROPT1D1	30	5	100	0.4	1.2	900	940	
L-31ROPT1D2	30	5	100	0.4	2	800	870	



L-51ROPT1X

Part No.	Min. Collector-Emitter Breakdown Voltage BV_{CEO} (V) @ $I_C=100\mu A$; $E_e=0$ mW/cm ²	Min. Emitter-Collector Breakdown Voltage BV_{ECO} (V) @ $I_C=100\mu A$; $E_e=0$ mW/cm ²	Max. Collector Dark Current I_{CEO} (nA) @ $V_{CE}=10V$; $E_e=0$ mW/cm ²	Max. Collector-Emitter Saturation Voltage $V_{CE(S)}$ (V) @ $I_C=2mA$; $E_e=0.5$ mW/cm ²	Typ. On State Collector Current I_C (mA) @ $V_{CE}=5V$; $E_e=0.1$ mW/cm ²	Spectral Sensitivity Wavelength λ_p (nm)		
						Min.	Typ.	Max.
L-51ROPT1C	30	5	100	0.4	2	400		1050
L-51ROPT1D1	30	5	100	0.4	1.2	900	940	
L-51ROPT1D2	30	5	100	0.4	1.2	800	870	

Photodiode



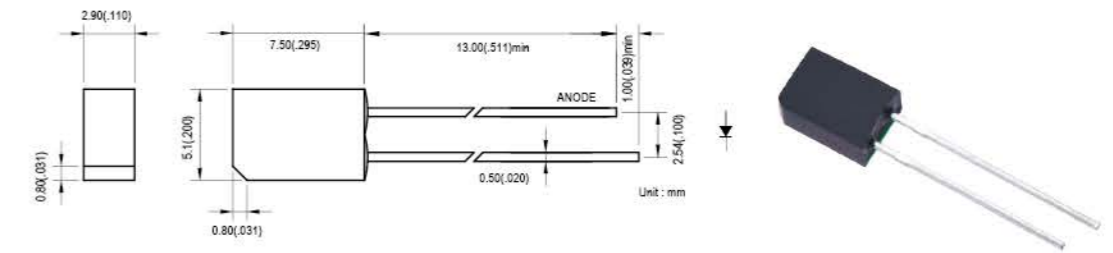
Application

- Smoking Detector
- Detecting Object

Applications

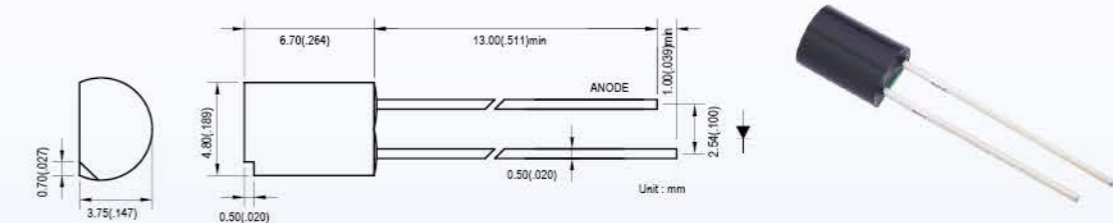


Photodiode



L-SB1R9PD1X

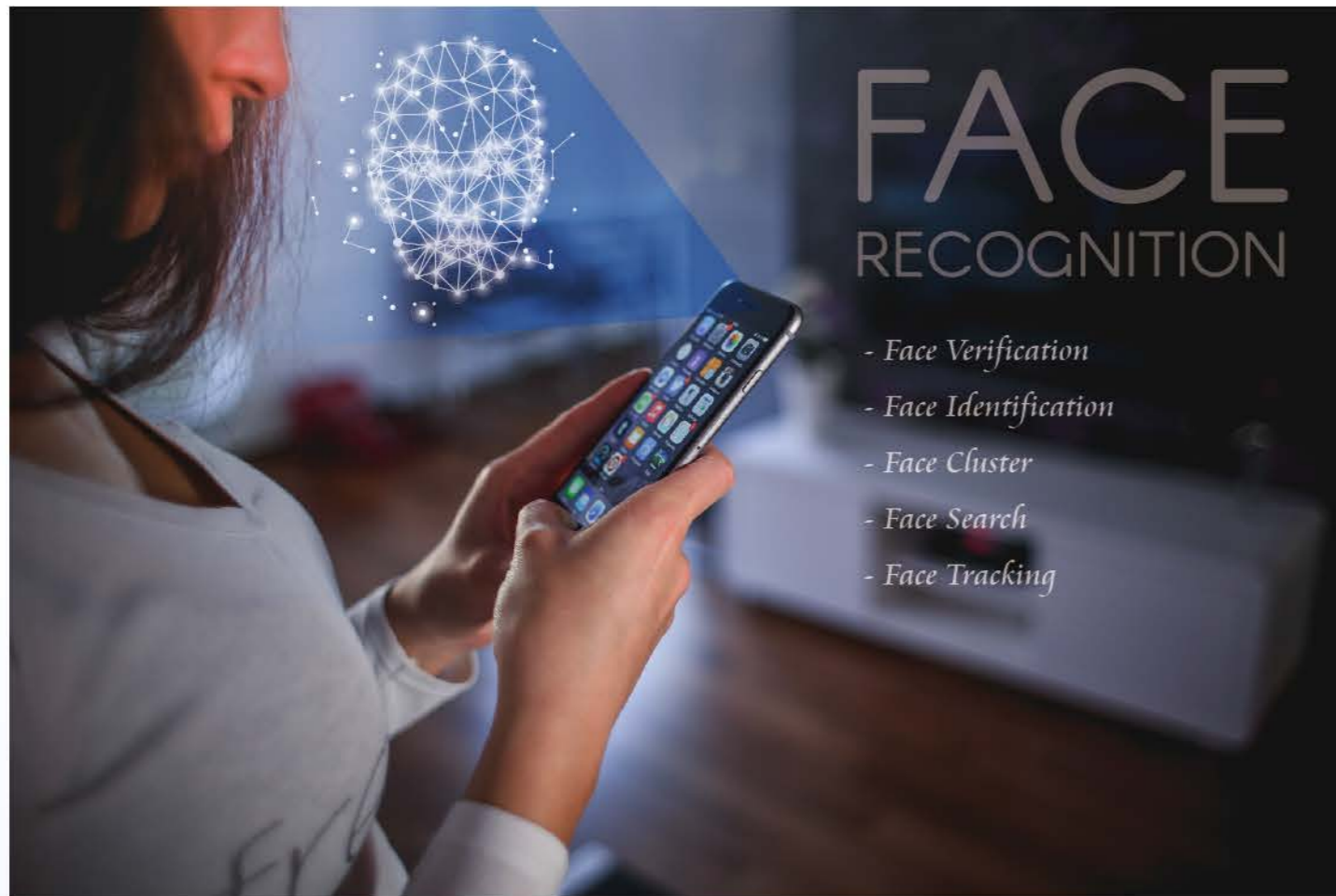
Part No.	Max. Reverse Dark Current I_D (nA) @ $V_R=10V$; $E_e=0$ mW/cm ²	Min. Reverse Voltage $V(BR)R$ (V) @ $I_R=100\mu A$; $E_e=0$ mW/cm ²	Typ. Open Circuit Voltage V_{OC} (V) @ $E_e=5$ mW/cm ²	Typ. Light Current I_L (μA) @ $V_R=5V$; $E_e=5$ mW/cm ²	Total Capacitance C_T (PF) @ $f=1$ mhz; $V_R=5V$; $E_e=0$ mW/cm ²	Spectral Sensitivity Wavelength λ_p (nm)		
						Min.	Typ.	Max.
L-SB1R9PD1C	30	33	390	40	18	400		1050
L-SB1R9PD1D1	30	33	390	40	18	900	940	
L-SB1R9PD1D2	30	33	390	40	18	800	870	



L-SC1R9PD1X

Part No.	Max. Reverse Dark Current I_D (nA) @ $V_R=10V$; $E_e=0$ mW/cm ²	Min. Reverse Voltage $V(BR)R$ (V) @ $I_R=100\mu A$; $E_e=0$ mW/cm ²	Typ. Open Circuit Voltage V_{OC} (V) @ $E_e=5$ mW/cm ²	Typ. Light Current I_L (μA) @ $V_R=5V$; $E_e=5$ mW/cm ²	Total Capacitance C_T (PF) @ $f=1$ mhz; $V_R=5V$; $E_e=0$ mW/cm ²	Spectral Sensitivity Wavelength λ_p (nm)		
						Min.	Typ.	Max.
L-SC1R9PD1C	30	33	390	40	18	400		1050
L-SC1R9PD1D1	30	33	390	40	18	900	940	
L-SC1R9PD1D2	30	33	390	40	18	800	870	

High Power Infrared

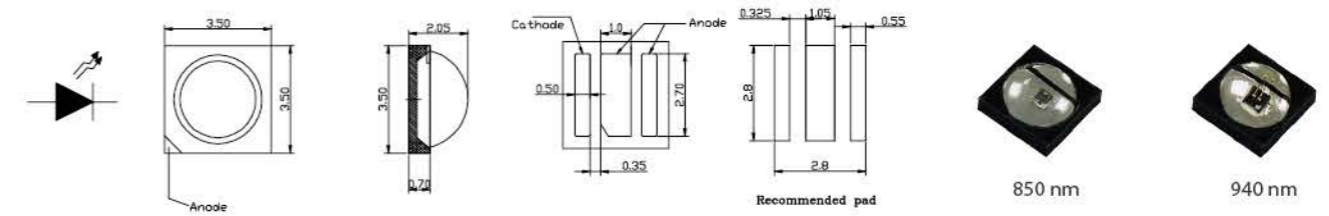


Application

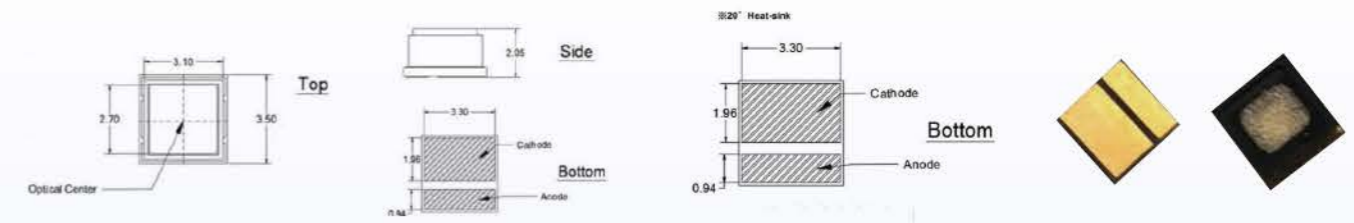
- Drowsy Driver Detection
- Iris Recognition
- Face Recognition
- AR / VR / Gesture Recognition / VCSEL 3D Sensing (TOF)
- Vein Stria Recognition



High Power Infrared



Part No.	test condition (IF)	Radiant Intensity(mW)	Wavelength(nm)	Viewing Angle(°)
LT3535IR4CT-N-P-E-B	350 mA	250 mW	850 nm	120
LT3535IR4CT-N-Y-E-B	350 mA	240 mW	850 nm	150
LT3535IR4CT-R-P-E-B	350 mA	195 mW	850 nm	120
LT3535IR4CT-R-Y-E-B	1000 mA	145 mW	850 nm	150
LT3535IR4CT-U-P-E-B	1000 mA	175 mW	850 nm	120
LT3535IR4CT-U-Y-E-B	1000 mA	165 mW	850 nm	150
LT3535IR1CT-N-Y-E-B	350 mA	40 mW	940 nm	150



Part No.	test condition (IF)	Radiant Intensity(mW)	Wavelength(nm)	Viewing Angle(°)
L-T3535IR1CT-55-72-1W-ZGY	1.25 mA	1000 mW	940 nm	55 / 72
L-T3535IR1CT-55-72-2W-ZGY	2.5 mA	2000 mW	940 nm	55 / 72



AR / VR / Gesture Recognition

Vein Stria Recognition

Drowsy Driver Detection

Mid Power - UVC

Mid Power - UVC



NEW LT3535UVC-KPC

NEW LT3535UVC-KPCA1

NEW LT3535UVC-K1PC

NEW LT3535UVC-K1PCA1

Application

- Ultraviolet disinfection
- Phototherapy
- Bio- Analysis/ Detection
- General use

Part No.	Package	test condition (IF)	Radiant Intensity(mW)	Wavelength(nm)	Viewing Angle(°)
LT3535UVC-KPC	SMD	80 mA	9.2 mW	275 nm	120
LT3535UVC-KPCA1	SMD	150 mA	18.4 mW	275 nm	120
LT3535UVC-K1PC	SMD	40 mA	4 mW	275 nm	120
LT3535UVC-K1PCA1	SMD	80 mA	8 mW	275 nm	120



Mid Power - UVC

Mid Power - UVC

NEW

LT3535UVC-KCCM

NEW

LT3535UVC-KPCM

Part No.	Package	test condition (IF)	Radiant Intensity(mW)	Wavelength(nm)	Viewing Angle(°)
LT3535UVC-KCCM	SMD	100 mA	20 mW	275nm	60
LT3535UVC-KPCM	SMD	100 mA	15 mW	275nm	120



NEW

LT5050UVC-XPC

NEW

LT5050UVC-XPCA1

Part No.	Package	test condition (IF)	Radiant Intensity(mW)	Wavelength(nm)	Viewing Angle(°)
LT5050UVC-XPC	SMD	350 mA	28 mW	275 nm	120
LT5050UVC-XPCA1	SMD	600 mA	80 mW	275 nm	120



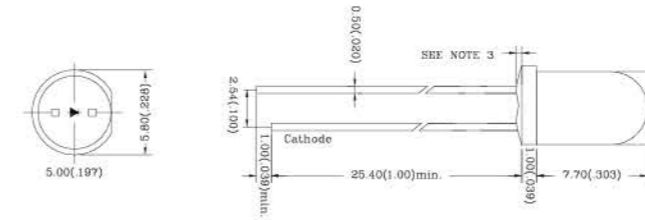
Low Power

Low Power



Application

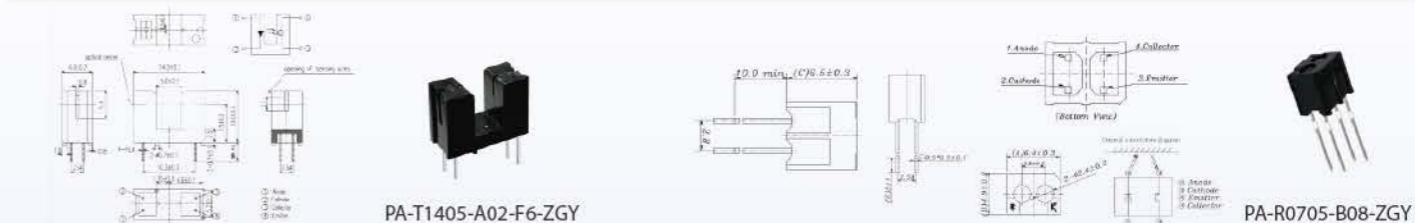
- Liquid Level Sensor
- Optical Sensor
- PM2.5 Sensor
- Avoidance Sensor
- Smoke Detector
- Servo Motor-Encoder
- Bit / Bubble Monitor Sensor



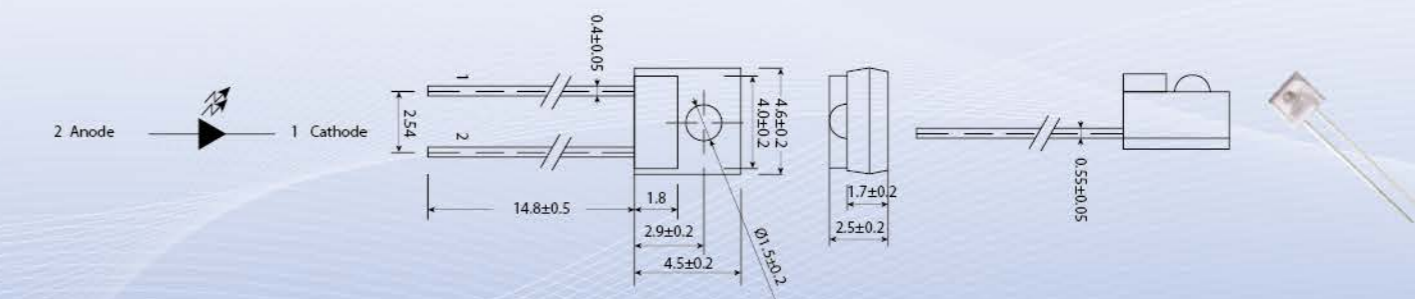
Part No.	Package	test condition (IF)	Radiant Intensity(mW/sr)	Wavelength(nm)	Viewing Angle(°)
L-514EIR1C	F5	20 mA	28 mW	940 nm	20
L-524EIR1C	F5	20 mA	28 mW	940 nm	20



Part No.	Package	Reverse Light Current (IL)	Wavelength(nm)	Viewing Angle(°)
L-SB1R12PD1D1-ZGY	DIP	25	840 nm ~ 1100 nm	120
L-C5042PDC-ZGY	SMD	25	400 nm ~ 1100 nm	120



Part No.	Package	Input (Emitter)	Output (Detector)	Tr / Tf (μs)
PA-T1405-A02-F6-ZGY	DIP	75 mW	50 mA	25 / 25
PA-R0705-B08-ZGY	DIP	75 mW	50 mA	25 / 25



Part No.	Package	test condition (IF)	Radiant Intensity(mW/sr)	Wavelength(nm)	Viewing Angle(°)
PL-LIRP28C-ZGY	DIP	20 mA	3.97 mW	940 nm	40

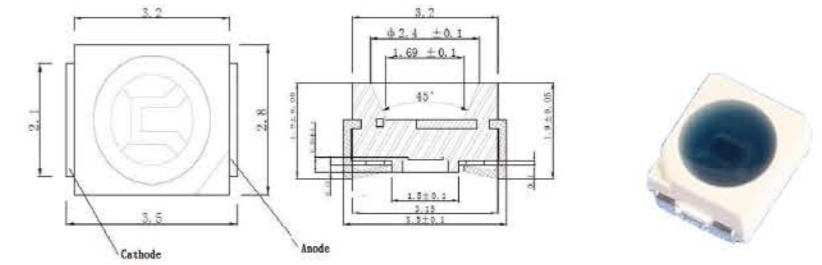
Ambient Light Sensor



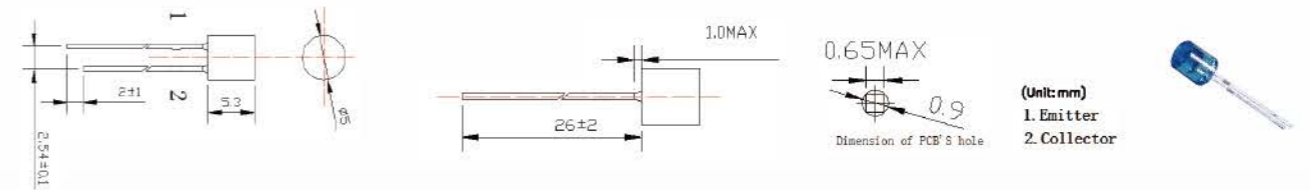
Application

- Detection of ALS to Control IR LED
- Automatic contrast for light change

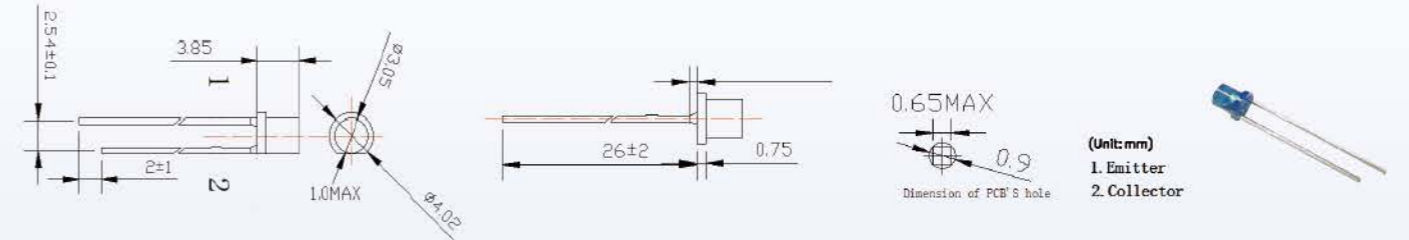
Ambient Light Sensor



Part No.	Package	On State Collector Current (Ev=30Lux)	Wavelength(nm)	Viewing Angle(°)
L-T670IRCT-JNJ	PLCC	15	550 nm	120



Part No.	Package	On State Collector Current (Ev=30Lux)	Wavelength(nm)	Viewing Angle(°)
L-5Q3IRT-JNJ	DIP	15	550 nm	120

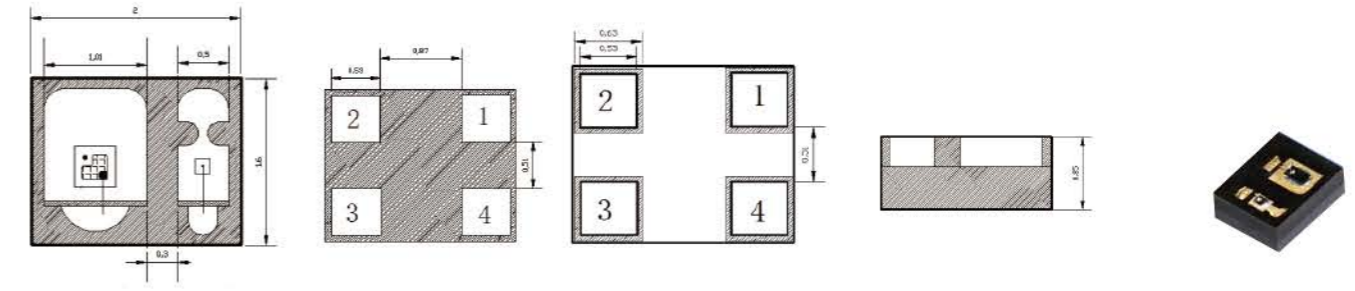


Part No.	Package	Radiant Intensity(mW/sr)	Wavelength(nm)	Viewing Angle(°)
L-334IRT-JNJ	DIP	15	550 nm	120



TWS Proximity Sensor

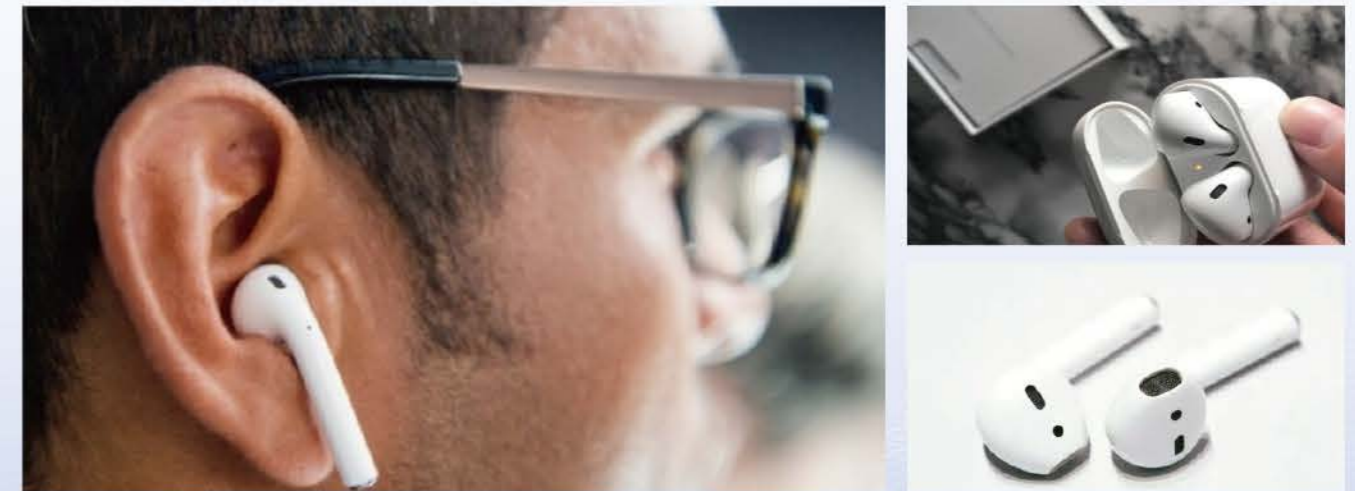
TWS Proximity Sensor



Part No.	Package	test condition (IF)	Radiant Intensity(mW)	Wavelength(nm)	Viewing Angle(°)
L-T2016IR1CT-JNJ	SMD	10 mA	12	940 nm	120

Application

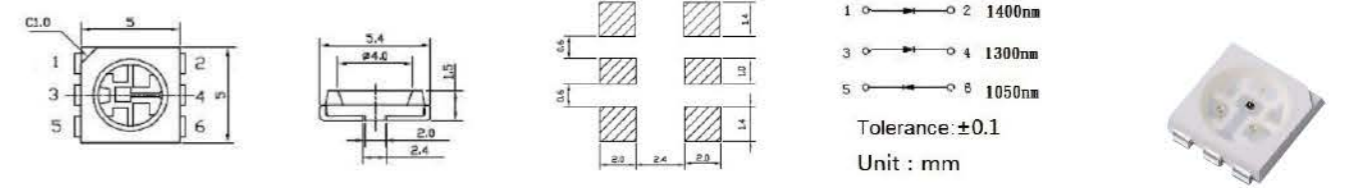
- TWS-Earphone
- Proximity Sensor



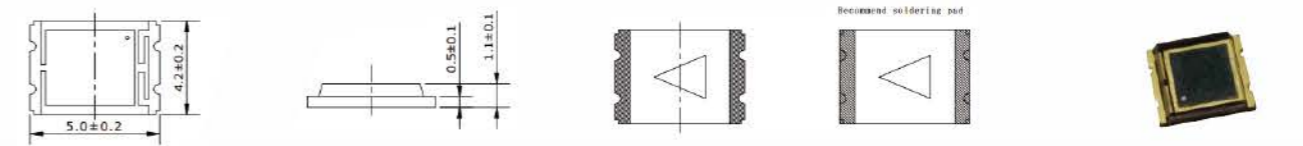
SMD PLCC



SMD PLCC



Part No.	Package	test condition (IF)	Radiant Intensity(mW)	Wavelength(nm)	Viewing Angle(°)
L-T69F3IN1CT-JNJ	PLCC	100 mA	33 / 34 / 25	1050 nm / 1300 nm / 1400 nm	120



Part No.	Package	Reverse Light Current (IL)	Wavelength(nm)	Viewing Angle(°)
L-C5042PDC-ZGY	SMD	25	400 nm ~ 1100 nm	120

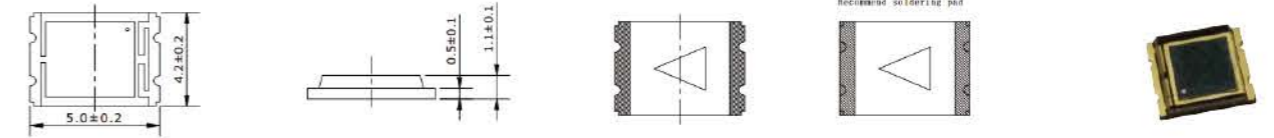
Application

- Food
- Skin Moisture
- Gas Measurement
- Blood Oxygen
- Pulse Sensor

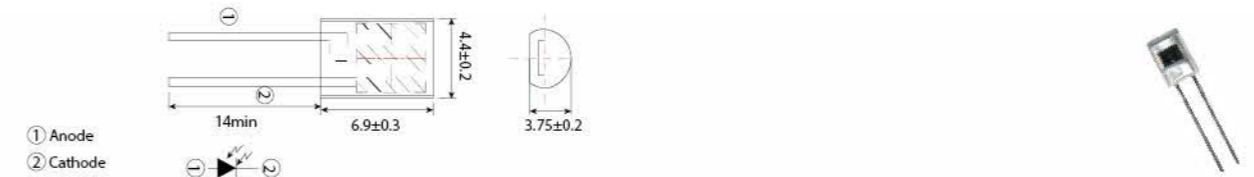


Automotive

Automotive



Part No.	Package	Reverse Light Current (IL)	Wavelength(nm)	Viewing Angle(°)
L-C5042PDC-ZGY	SMD	25	400 nm ~ 1100 nm	120



Part No.	Package	Reverse Light Current (IL)	Wavelength(nm)	Viewing Angle(°)
L-SC1R12PD1C-ZGY(AM)	DIP	25	400 nm ~ 1100 nm	120

Application

- Sunlight Sensor-Air Condition
- Rain Sensor / Anti-Glare Sensor
- Sunlight Sensor-Headlight



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